



# PJL9602

## 30V Complementary Enhancement Mode MOSFET

Voltage    30 / -30V    Current    6.1 /-6.0A

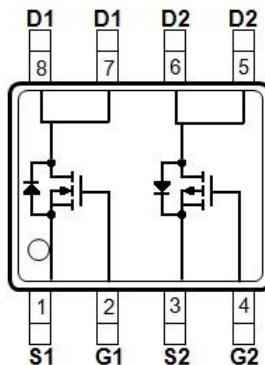
### Features

- Advanced Trench Process Technology
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case: SOP-8 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams

SOP-8



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	N-CH LIMIT	P-CH LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	30	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current <small><math>T_a=25^\circ\text{C}</math></small>	$I_D$	6.1	-6.0	A
	$I_D$	4.9	-4.7	A
Pulsed Drain Current <small>(Note 4)</small>	$I_{DM}$	24.4	-24	A
Power Dissipation <small><math>T_a=25^\circ\text{C}</math></small>	$P_D$	1.7		W
		1.1		
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150		°C
Thermal resistance - Junction to Ambient <small>(Note 3)</small>	$R_{\theta JA}$	73.5		°C/W



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## N-Channel Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.3	2.1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=6.0A$	-	23	28	$m\Omega$
		$V_{GS}=4.5V, I_D=3.0A$	-	36	43	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1.0	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=6A,$ $V_{GS}=10V$ (Note 3)	-	7.8	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.2	-	
Gate-Drain Charge	$Q_{gd}$		-	1.5	-	
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	343	-	pF
Output Capacitance	$C_{oss}$		-	48	-	
Reverse Transfer Capacitance	$C_{rss}$		-	34	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=6A,$ $V_{GS}=10V, R_G=3\Omega$ (Note 3)	-	3	-	ns
Turn-On Rise Time	$tr$			40	-	
Turn-Off Delay Time	$t_{d(off)}$			38	-	
Turn-Off Fall Time	$tf$		-	39	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_s$	---	-	-	6.1	A
Diode Forward Voltage	$V_{SD}$	$I_s=1.0A, V_{GS}=0V$	-	0.78	1.2	V



## PJL9602

### P-Channel Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.6	-2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4A$	-	26	30	$m\Omega$
		$V_{GS}=-4.5V, I_D=-2A$	-	36	45	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1.0	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-15V, I_D=-5A,$ $V_{GS}=-4.5V$ (Note 1,2)	-	7.8	-	nC
Gate-Source Charge	$Q_{gs}$		-	2.7	-	
Gate-Drain Charge	$Q_{gd}$		-	2.8	-	
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V,$ $f=1.0MHz$	-	870	-	pF
Output Capacitance	$C_{oss}$		-	130	-	
Reverse Transfer Capacitance	$C_{rss}$		-	93	-	
Turn-On Delay Time	$td_{(on)}$	$V_{DS}=-15V, ID=-1A,$ $V_{GS}=-10V, R_G=6\Omega$ (Note 1,2)	-	6.5	-	ns
Turn-On Rise Time	$tr$		-	8.8	-	
Turn-Off Delay Time	$td_{(off)}$		-	73	-	
Turn-Off Fall Time	$tf$		-	44	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_s$	---	-	-	-6.2	A
Diode Forward Voltage	$V_{SD}$	$I_s=1A, V_{GS}=0V$	-	-0.75	-1.0	V

#### NOTES :

1. Pulse width $\leq 300\mu s$ , Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. Repetitive rating, pulse width limited by junction temperature  $T_J(MAX)=150^\circ C$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J=25^\circ C$ .
5.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.



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## N-CH TYPICAL CHARACTERISTIC CURVES

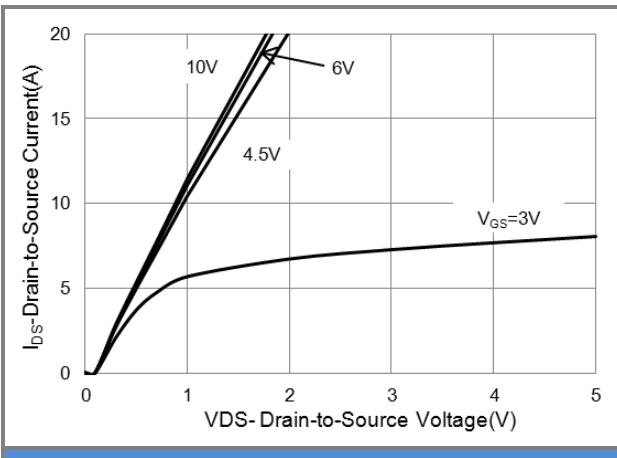


Fig.1 On-Region Characteristics

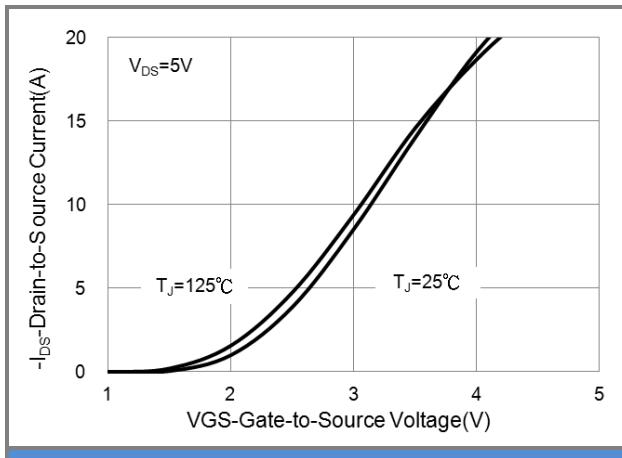


Fig.2 Transfer Characteristics

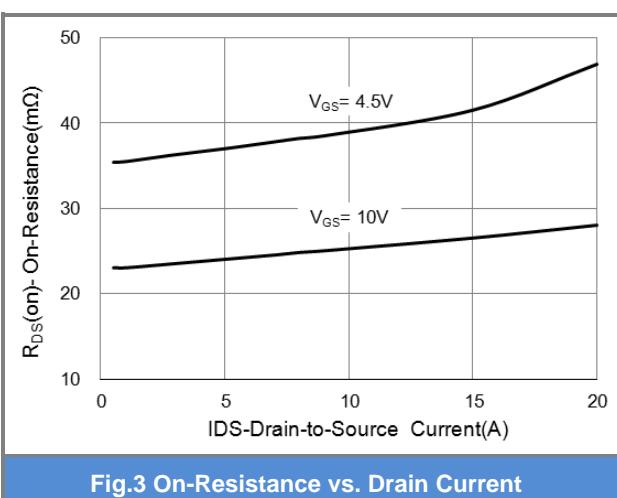


Fig.3 On-Resistance vs. Drain Current

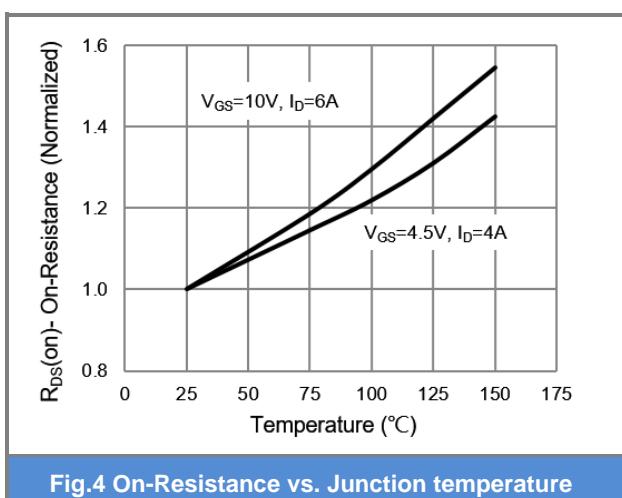


Fig.4 On-Resistance vs. Junction temperature

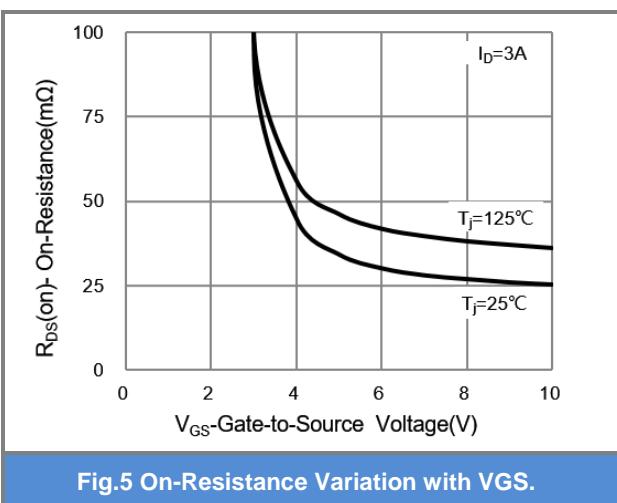


Fig.5 On-Resistance Variation with V<sub>GS</sub>.

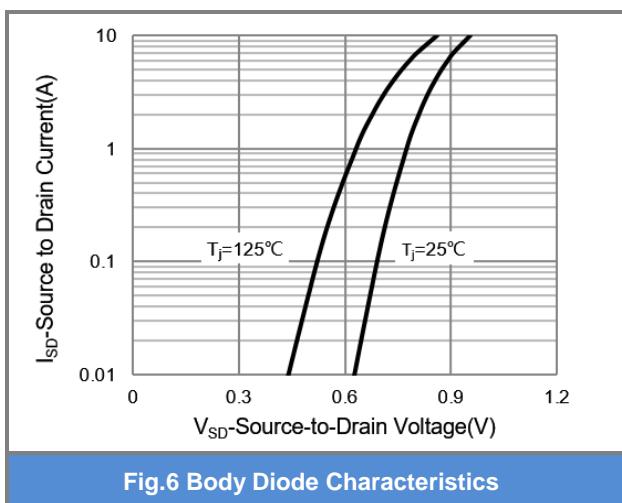


Fig.6 Body Diode Characteristics



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## TYPICAL CHARACTERISTIC CURVES

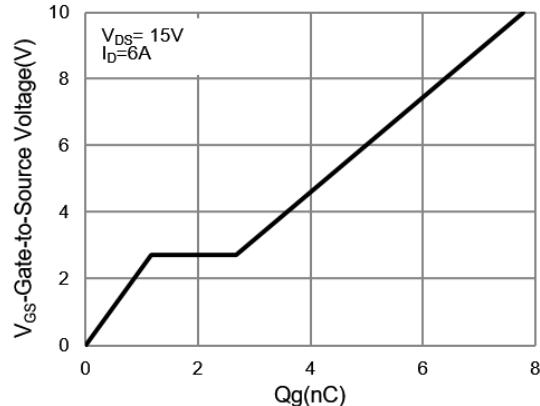


Fig.7 Gate-Charge Characteristics

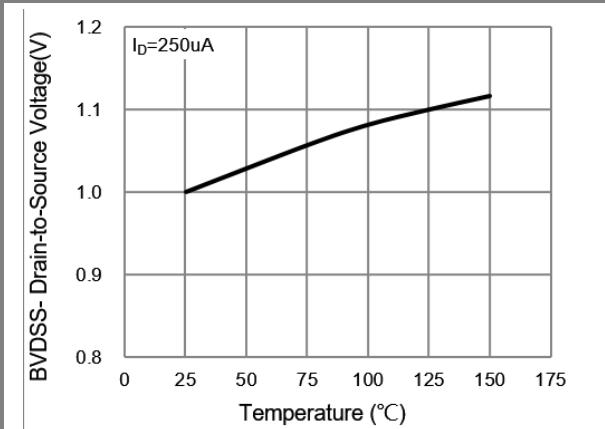


Fig.8 Breakdown Voltage Variation vs. Temperature

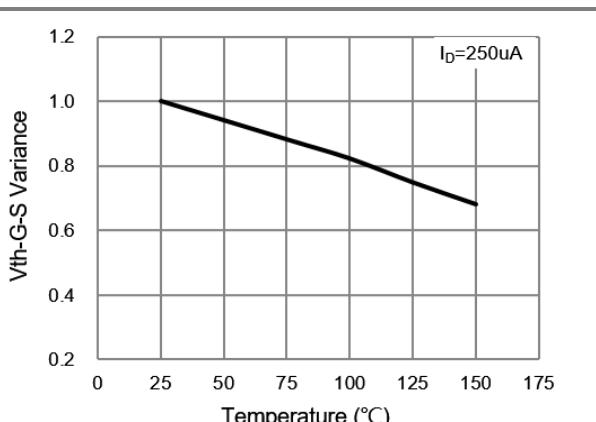


Fig.9 Threshold Voltage Variation with Temperature.

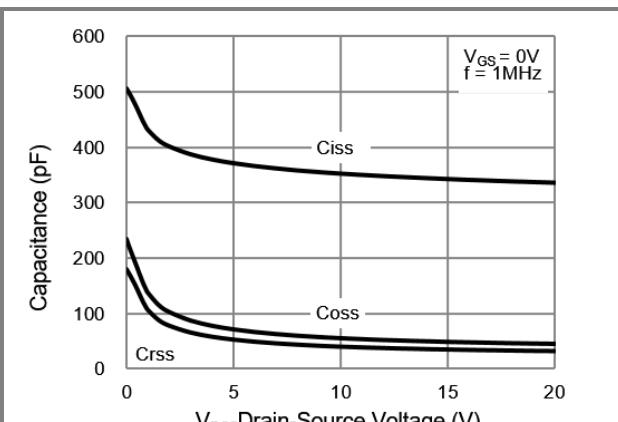


Fig.10 Capacitance vs. Drain-Source Voltage.



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## P-CH TYPICAL CHARACTERISTIC CURVES

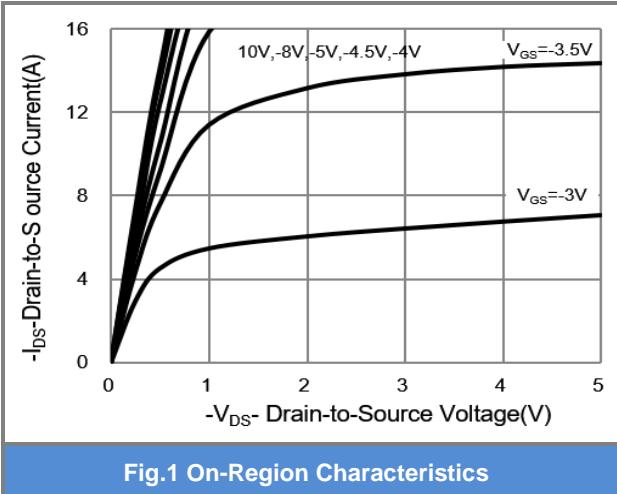


Fig.1 On-Region Characteristics

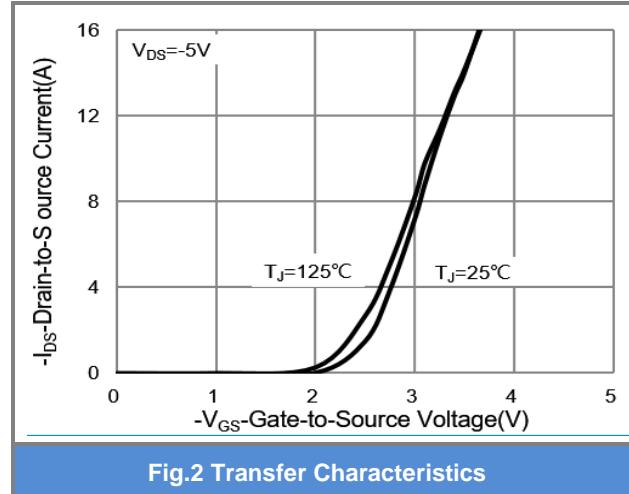


Fig.2 Transfer Characteristics

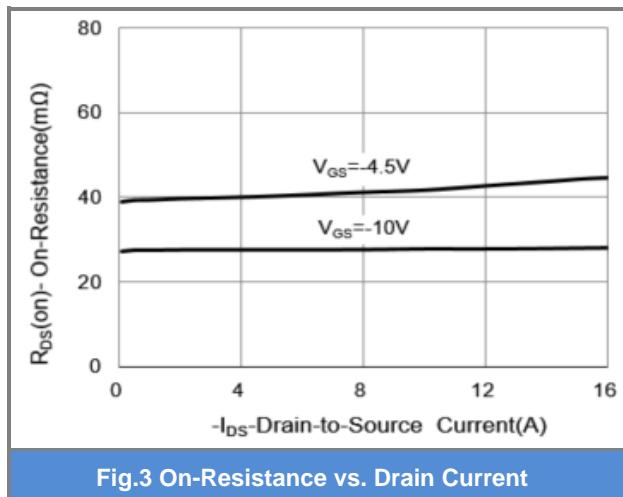


Fig.3 On-Resistance vs. Drain Current

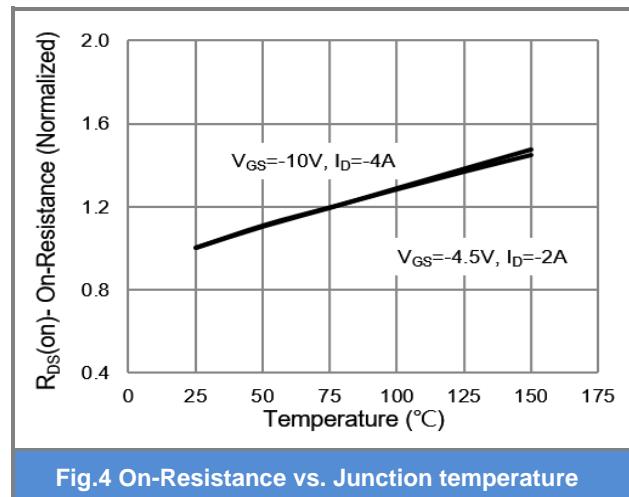


Fig.4 On-Resistance vs. Junction temperature

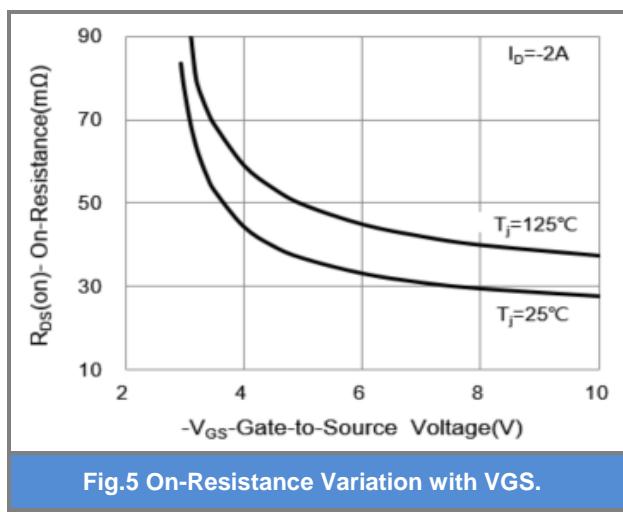


Fig.5 On-Resistance Variation with VGS.

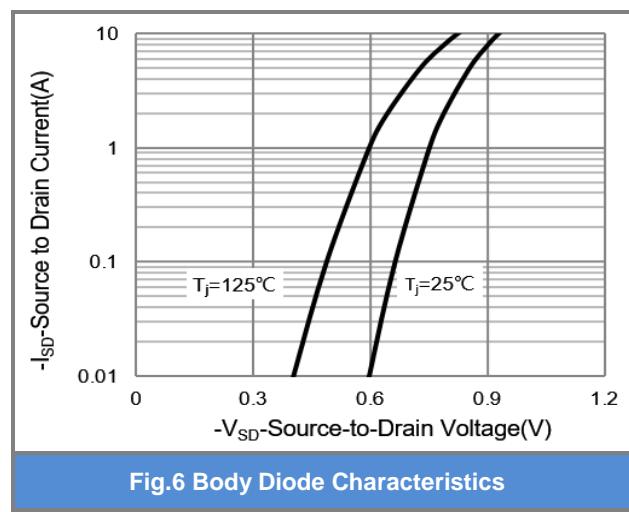


Fig.6 Body Diode Characteristics



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## TYPICAL CHARACTERISTIC CURVES

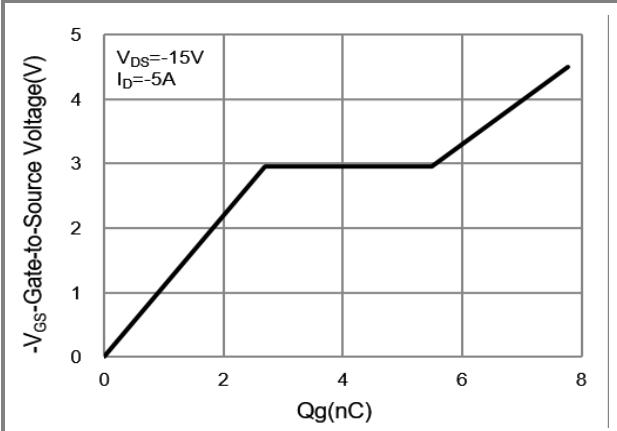


Fig.7 Gate-Charge Characteristics

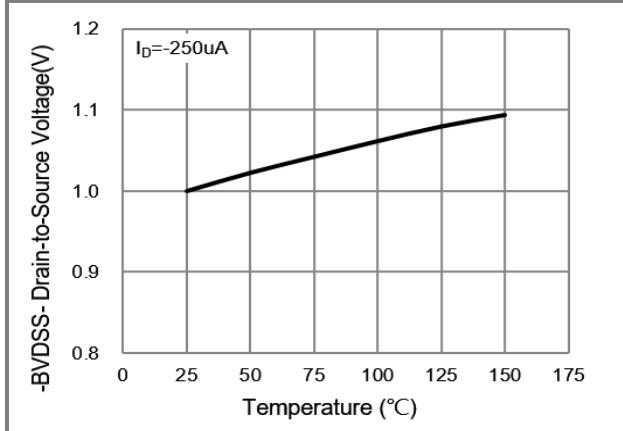


Fig.8 Threshold Voltage Variation with Temperature

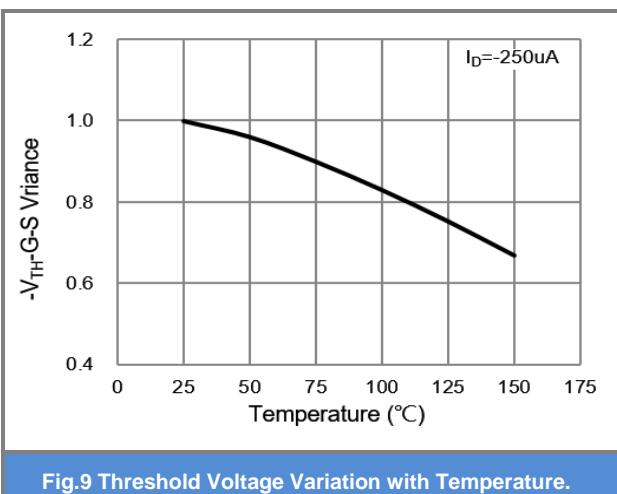


Fig.9 Threshold Voltage Variation with Temperature.

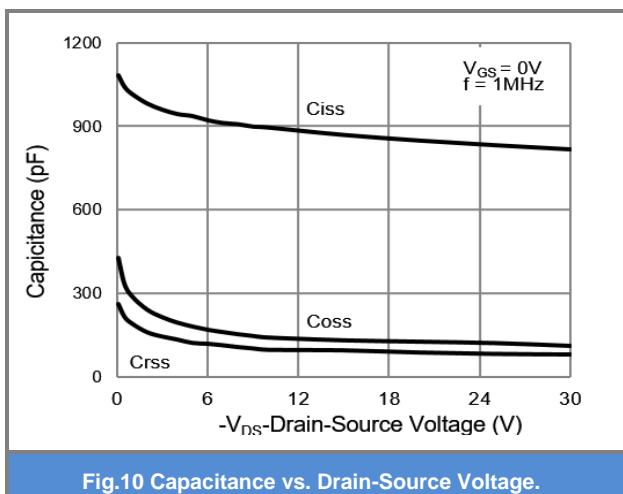


Fig.10 Capacitance vs. Drain-Source Voltage.

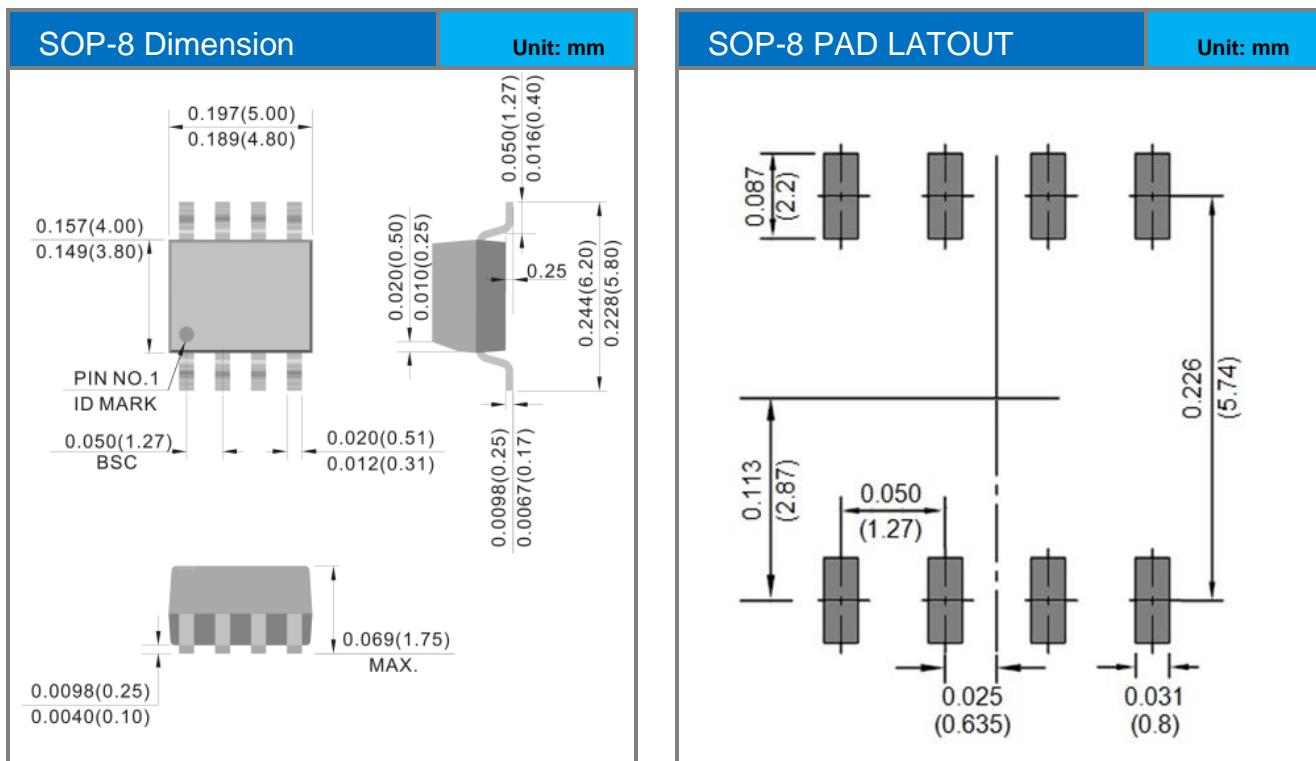


# PJL9602

## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJL9602_R2_00001	SOP-8	2.5K pcs / 13" reel	L9602	Halogen free

## MOUNTING PAD LAYOUT





## PJL9602

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